

Yu-Long Jiang

List of Publications by Year in descending order

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Version: 2024-02-01

21
papers

162
citations

1307594

7
h-index

1125743

13
g-index

21
all docs

21
docs citations

21
times ranked

136
citing authors

#	ARTICLE	IF	CITATIONS
1	TiSi(Ge) Contacts Formed at Low Temperature Achieving Around $2 \times 10^{-9} \sim \Omega \text{ cm}^2$ Contact Resistivities to p-SiGe. IEEE Transactions on Electron Devices, 2017, 64, 500-506.	3.0	31
2	Lanthanum and Lanthanum Silicide Contacts on N-Type Silicon. IEEE Electron Device Letters, 2017, 38, 843-846.	3.9	28
3	Ultra-Low Contact Resistivity of $0.1 \sim \Omega \cdot \text{mm}$ for Au-Free Ti _x Al _y Alloy Contact on Non-Recessed i-AlGaIn/GaN. IEEE Electron Device Letters, 2020, 41, 143-146.	3.9	24
4	A Novel One-Transistor Active Pixel Sensor With <i>In-Situ</i> Photoelectron Sensing in 22 nm FD-SOI Technology. IEEE Electron Device Letters, 2019, 40, 738-741.	3.9	23
5	Effective Schottky Barrier Height Lowering by TiN Capping Layer for TiSi ₂ /Si Power Diode. IEEE Electron Device Letters, 2015, 36, 597-599.	3.9	8
6	Thermal Stability of TiN/Ti _p ⁺ -Si _{0.3} Ge _{0.7} Contact With Ultralow Contact Resistivity. IEEE Electron Device Letters, 2018, 39, 83-86.	3.9	8
7	Difference Between Atomic Layer Deposition TiAl and Physical Vapor Deposition TiAl in Threshold Voltage Tuning for Metal Gated NMOSFETs. IEEE Electron Device Letters, 2021, 42, 1830-1833.	3.9	7
8	Improved Ohmic Performance by the Metallic Bilayer Contact Stack of Oxygen-Incorporated La/Ultrathin TiSi ₂ on n-Si. IEEE Transactions on Electron Devices, 2018, 65, 1869-1872.	3.0	6
9	A Novel One-Transistor Active Pixel Sensor With Tunable Sensitivity. IEEE Electron Device Letters, 2021, 42, 927-930.	3.9	6
10	Very-Low Resistance Contact to 2D Electron Gas by Annealing Induced Penetration Without Spikes Using TaAl/Au on Non-Recessed i-AlGaIn/GaN. IEEE Electron Device Letters, 2020, 41, 1484-1487.	3.9	5
11	Performance Improvement by Cold Xe Pre-Amorphization Implant for Nickel Silicidation of 28-nm PMOSFET. IEEE Electron Device Letters, 2019, 40, 777-779.	3.9	4
12	Significant Performance Improvement of MicroRNA-375 Detection by Modulation of Au Nanoparticle Distribution Using Silicon-on-Insulator MOSFET. IEEE Electron Device Letters, 2022, 43, 128-130.	3.9	3
13	Optimization of Ni(Pt)/Si-cap/SiGe Silicidation for pMOS Source/Drain Contact. IEEE Transactions on Electron Devices, 2017, 64, 2067-2071.	3.0	2
14	KrF Photoresist Profile Modulation by NH ₃ Plasma Treatment for 28 nm SRAM. IEEE Transactions on Semiconductor Manufacturing, 2018, 31, 266-269.	1.7	2
15	Effective Contact Resistivity Reduction for Mo/Pd/n-In _{0.53} Ga _{0.47} as Contact. IEEE Electron Device Letters, 2019, 40, 1800-1803.	3.9	2
16	Investigation of Ni(Pt)/Si-cap/SiGe solid phase reaction. , 2014, , .		1
17	Thermal Stability Improvement Induced by Laser Annealing for 50-Å... Ni(Pt) Film Silicidation. IEEE Transactions on Electron Devices, 2016, 63, 751-754.	3.0	1
18	Oxygen Gettering Cap to Scavenge Parasitic Oxide Interlayer in TiSi Contacts. IEEE Electron Device Letters, 2019, 40, 1712-1715.	3.9	1

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19	Significant Threshold Voltage Shift Induced by Ge Penetration into PMOSFET Channel of 28 nm SRAM. IEEE Electron Device Letters, 2018, , 1-1.	3.9	0
20	Performance Improvement by Blanket Boron Implant in the Sigma-Shaped Trench Before the Embedded SiGe Source/Drain Formation for 28-nm PMOSFET. IEEE Electron Device Letters, 2020, 41, 796-799.	3.9	0
21	DDDMOSFET Performance Improvement by Gate Oxide Removal Followed by Silicided Source/Drain Formation in Gate Slots. IEEE Transactions on Electron Devices, 2022, 69, 5368-5372.	3.0	0